

*B1  
(cont'd)*  
contact layer being thinner than the impurity layer and having a higher impurity concentration than the impurity layer;

a first electrode formed on the contact layer; and

a second electrode formed at another surface of the semiconductor substrate for allowing a current to flow between the first and second electrodes.

*Sub B1*  
11. (Amended) The electrode contact section according to claim 7, wherein the impurity layer has a thickness of not more than  $1.0 \mu\text{m}$  from the one surface of the semiconductor substrate.

12. (Amended) The electrode contact section according to claim 7, wherein the contact layer has a thickness of not more than  $0.2 \mu\text{m}$  from the one surface of the semiconductor substrate.

13. (Twice Amended) The electrode contact section according to claim 7, wherein: the silicide layer has a thickness of not more than  $0.2 \mu\text{m}$  from the one surface of the semiconductor substrate, and

the silicide layer is thinner than the contact layer

16. (Amended) A semiconductor device comprising:

a first-conductivity-type semiconductor substrate;

*39*  
a second-conductivity-type base region formed in one surface of the semiconductor substrate;

a first-conductivity-type impurity region formed in the base region;

a first electrode connected to the first-conductivity-type impurity region;

a gate electrode connected to the base region via an insulation film;

a second-conductivity-type impurity region formed in another surface of the semiconductor substrate and having a thickness of not more than  $1.0 \mu\text{m}$  from the another surface of the semiconductor substrate;

*31  
(cont.)*

a second-conductivity-type contact region formed in the second-conductivity-type impurity region and having a thickness of not more than 0.2  $\mu\text{m}$  from the another surface of the semiconductor substrate, the contact region being thinner than the second-conductivity-type impurity region and having a higher impurity concentration than the second-conductivity-type impurity region; and

a second electrode formed on the contact region.

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*B10*

18. (Amended) The semiconductor device according to claim 16, wherein the second-conductivity-type impurity region is formed in the entire another surface of the semiconductor substrate.

19. (Amended) The semiconductor device according to claim 16, wherein the impurity region is formed in a portion less than the entire another surface of the semiconductor substrate.

20. (Amended) A semiconductor device comprising:

a first-conductivity-type semiconductor substrate;

a second-conductivity-type base region formed in one surface of the semiconductor substrate;

a first-conductivity-type impurity region formed in the base region;

a first electrode connected to the first-conductivity-type impurity region;

a gate electrode connected to the base region via an insulation film;

a second-conductivity-type impurity region formed in another surface of the semiconductor substrate;

a second-conductivity-type contact region formed in the impurity region, the second-conductivity-type contact region being thinner than the second-conductivity-type impurity region and having a higher impurity concentration than the second-conductivity-type impurity region;

*(B) (C)*  
a second electrode formed on the contact region; and  
a silicide region formed between the second electrode and the contact region, the silicide region having a contact-region-side end thereof made to substantially correspond to that portion of the contact region at which a concentration profile of the contact region assumes a peak value.

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*B 11*  
22. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region has a thickness of not more than 1.0  $\mu\text{m}$  from the another surface of the semiconductor substrate.

*B*  
23. (Amended) The semiconductor device according to claim 20, wherein the contact region has a thickness of not more than 0.2  $\mu\text{m}$  from the another surface of the semiconductor substrate.

24. (Amended) The semiconductor device according to claim 20, wherein:  
the silicide region has a thickness of not more than 0.2  $\mu\text{m}$  from the another surface of the semiconductor substrate, and  
the silicide layer is thinner than the contact region.

25. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region is formed in the entire another surface of the semiconductor substrate.

26. (Amended) The semiconductor device according to claim 20, wherein the second-conductivity-type impurity region is formed in a portion less than the entire another surface of the semiconductor substrate.

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#### REMARKS

Favorable reconsideration of this application is respectfully requested.

The specification has been amended to correct minor informalities.